

40V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D $T_A = 25^\circ C$
-40V	50m Ω @ $V_{GS} = -10V$	-6.0A
	79m Ω @ $V_{GS} = -4.5V$	-4.7A

Features and Benefits

- Low on-resistance
- Fast switching speed
- “Green” component and RoHS compliant (Note 1)
- Qualified to AEC-Q101 Standards for High Reliability

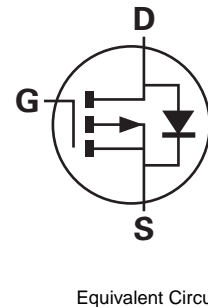
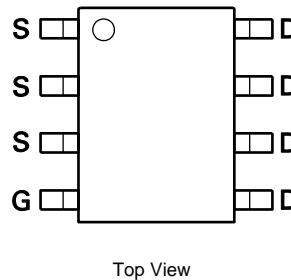
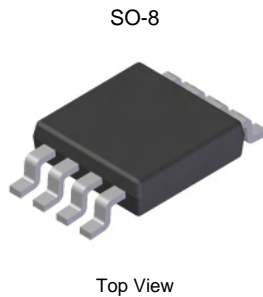
Description and Applications

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor control
- Backlighting
- DC-DC Converters
- Power management functions

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See diagram below
- Terminals: Finish - Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.074 grams (approximate)

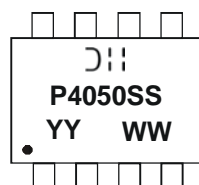


Ordering Information (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMP4050SSS-13	P4050SS	13	12	2,500

Note: 1. Diodes, Inc. defines “Green” products as those which are RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.’s “Green” Policy can be found on our website. For packaging details, go to our website.

Marking Information



⌋⌋ = Manufacturer’s Marking
P4050SS = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 09 = 2009)
WW = Week (01-53)

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

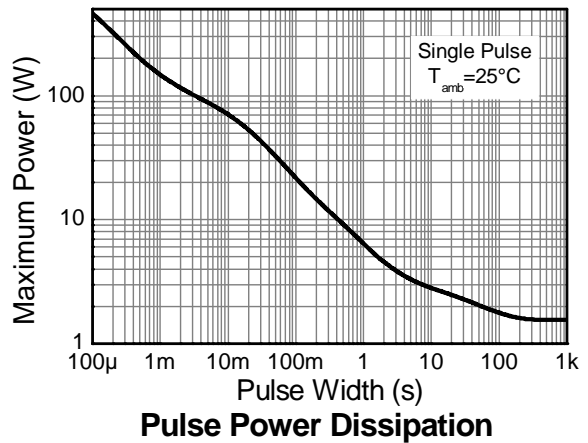
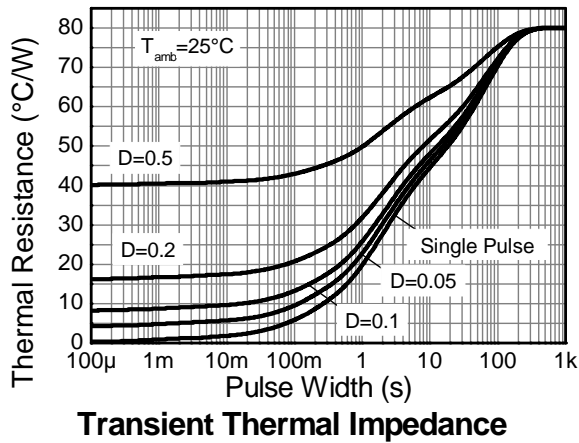
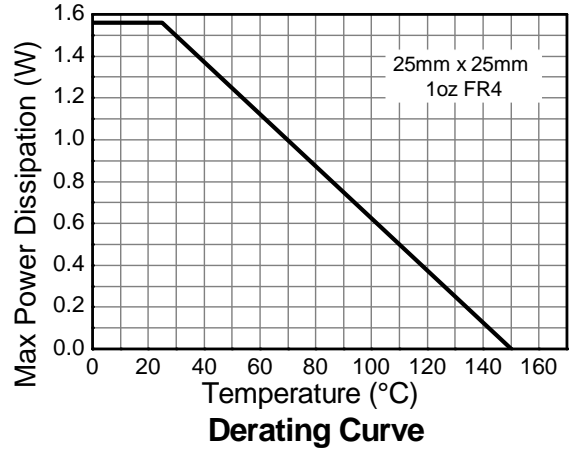
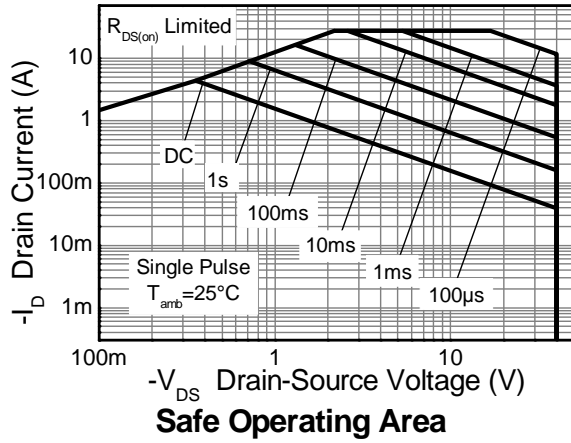
Characteristic		Symbol	Value	Unit	
Drain-Source voltage		V_{DSS}	-40	V	
Gate-Source voltage		V_{GS}	± 20	V	
Continuous Drain current	$V_{GS} = 10\text{V}$	(Note 2)	-6.0	A	
		(Note 4)	-4.8		
		$T_A = 70^\circ\text{C}$ (Note 4)	-4.4		
Pulsed Drain current	$V_{GS} = 10\text{V}$	(Note 5)	I_{DM}	-27.0	A
Continuous Source current (Body diode)		(Note 4)	I_S	-4.0	A
Pulsed Source current (Body diode)		(Note 5)	I_{SM}	-27.0	A

Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic		Symbol	Value	Unit
Power dissipation	(Note 3)	P_D	1.56	W
	(Note 4)		12.5	
Linear derating factor	(Note 3)	$R_{\theta JA}$	2.8	$\text{mW}/^\circ\text{C}$
	(Note 4)		22.5	
Thermal Resistance, Junction to Ambient	(Note 3)	$R_{\theta JL}$	80	$^\circ\text{C}/\text{W}$
	(Note 4)		44.5	
Thermal Resistance, Junction to Lead	(Note 6)	$R_{\theta JL}$	35	$^\circ\text{C}/\text{W}$
Operating and storage temperature range		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

- Notes:
- AEC-Q101 V_{GS} maximum is $\pm 16\text{V}$.
 - For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 - Same as note (3), except the device is measured at $t \leq 10$ sec.
 - Same as note (3), except the device is pulsed with $D = 0.02$ and pulse width 300 μs . The pulse current is limited by the maximum junction temperature.
 - Thermal resistance from junction to solder-point (at the end of the drain lead).

Thermal Characteristics

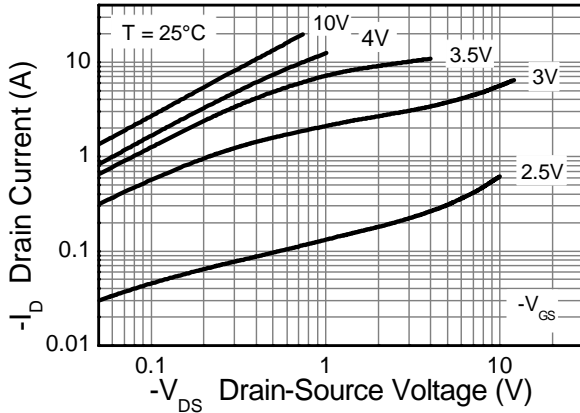


Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

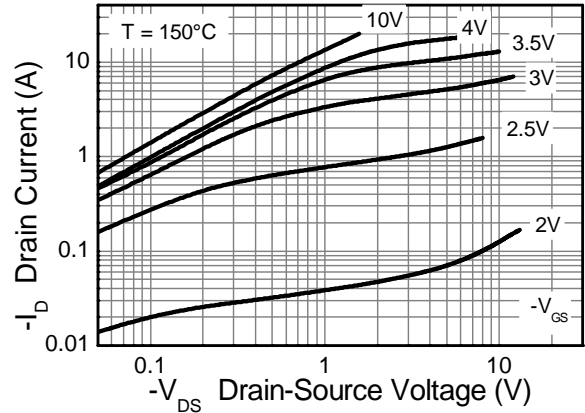
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	-40	—	—	V	$I_D = -250\mu\text{A}$, $V_{GS} = 0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-0.5	μA	$V_{DS} = -40\text{V}$, $V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(th)}$	-1.0	—	-3.0	V	$I_D = -250\mu\text{A}$, $V_{DS} = V_{GS}$
Static Drain-Source On-Resistance (Note 7)	$R_{DS(on)}$	—	0.038	0.050	Ω	$V_{GS} = -10\text{V}$, $I_D = -6\text{A}$
			0.055	0.079		$V_{GS} = -4.5\text{V}$, $I_D = -5\text{A}$
Forward Transconductance (Notes 7 & 8)	g_{fs}	—	14	—	S	$V_{DS} = -15\text{V}$, $I_D = -6\text{A}$
Diode Forward Voltage (Note 7)	V_{SD}	—	-0.86	-1.2	V	$I_S = -6\text{A}$, $V_{GS} = 0\text{V}$
Reverse recovery time (Note 8)	t_{rr}	—	18.5	—	ns	$I_S = -2.5$, $di/dt = 100\text{A}/\mu\text{s}$
Reverse recovery charge (Note 8)	Q_{rr}	—	15.6	—	nC	
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	674	—	pF	$V_{DS} = -20\text{V}$, $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$
Output Capacitance	C_{oss}	—	115	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	67.7	—	pF	
Total Gate Charge (Note 9)	Q_g	—	6.9	—	nC	$V_{GS} = -4.5\text{V}$
Total Gate Charge (Note 9)	Q_g	—	13.9	—	nC	$V_{GS} = -10\text{V}$
Gate-Source Charge (Note 9)	Q_{gs}	—	2	—	nC	
Gate-Drain Charge (Note 9)	Q_{gd}	—	3.4	—	nC	
Turn-On Delay Time (Note 9)	$t_{D(on)}$	—	1.9	—	ns	$V_{DD} = -20\text{V}$, $V_{GS} = -10\text{V}$ $I_D = -1\text{A}$, $R_G \cong 6.0\Omega$
Turn-On Rise Time (Note 9)	t_r	—	3.1	—	ns	
Turn-Off Delay Time (Note 9)	$t_{D(off)}$	—	31.5	—	ns	
Turn-Off Fall Time (Note 9)	t_f	—	12.6	—	ns	

- Notes:
7. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$
 8. For design aid only, not subject to production testing.
 9. Switching characteristics are independent of operating junction temperatures.

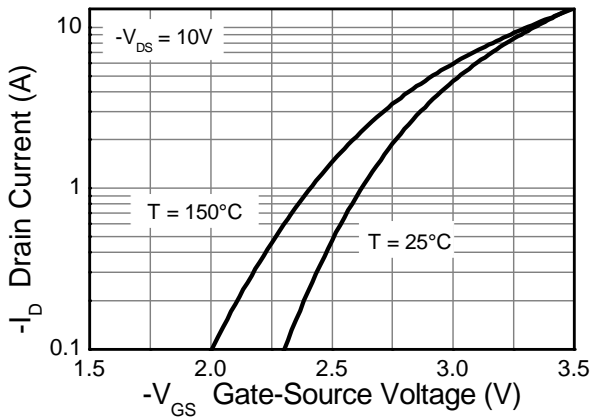
Typical Characteristics



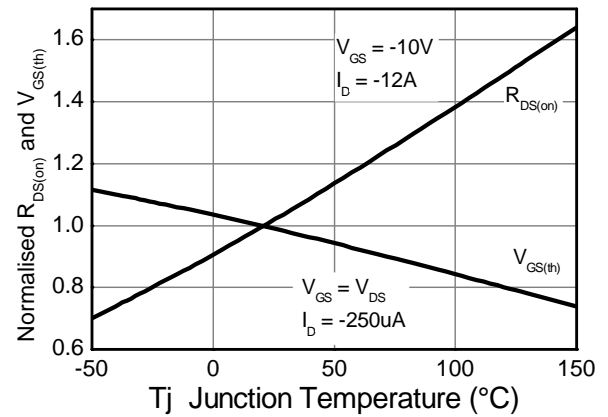
Output Characteristics



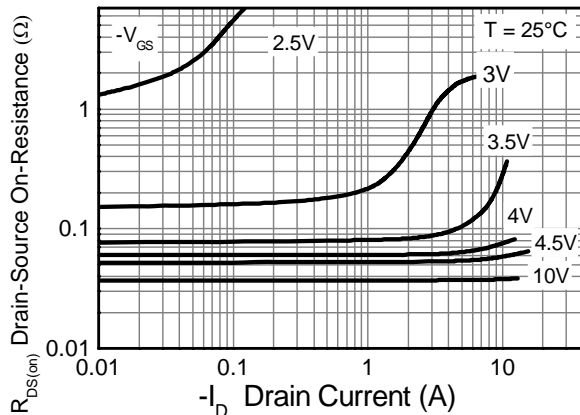
Output Characteristics



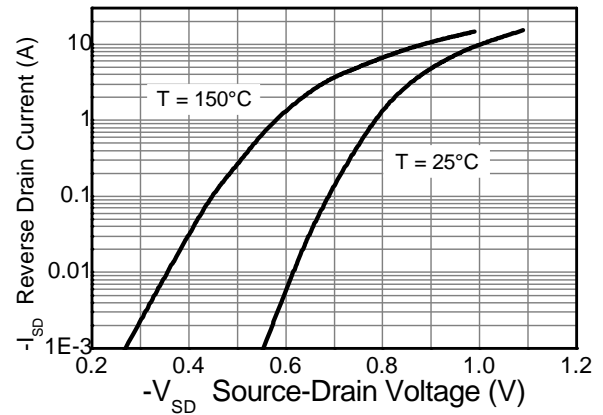
Typical Transfer Characteristics



Normalised Curves v Temperature

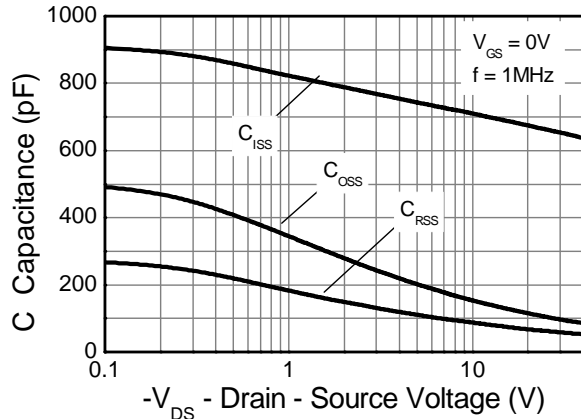


On-Resistance v Drain Current

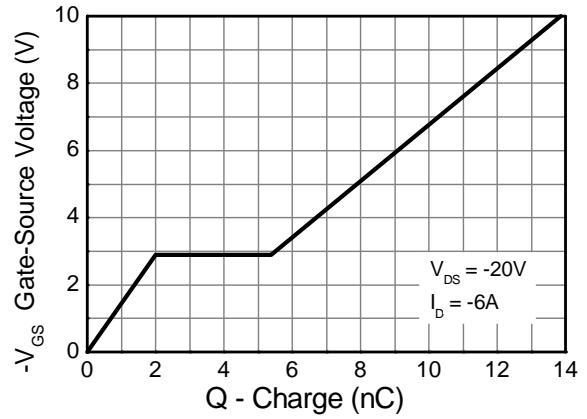


Source-Drain Diode Forward Voltage

Typical Characteristics - continued

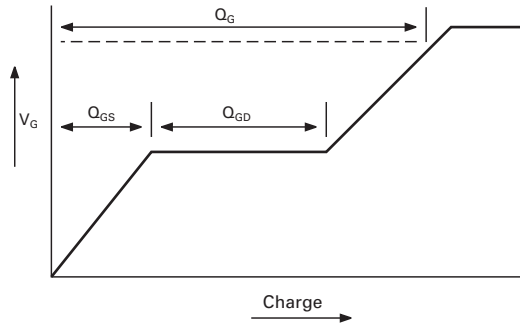


Capacitance v Drain-Source Voltage

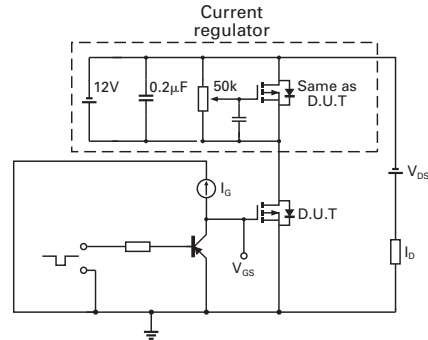


Gate-Source Voltage v Gate Charge

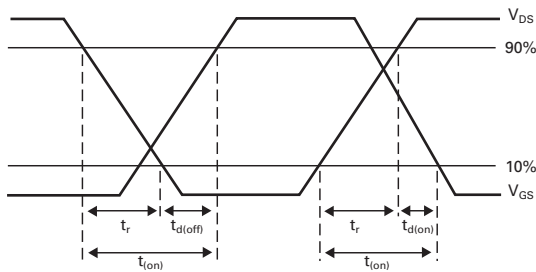
Test Circuits



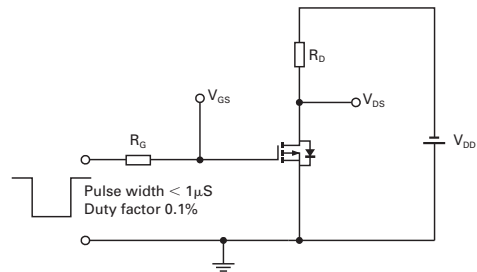
Basic gate charge waveform



Gate charge test circuit

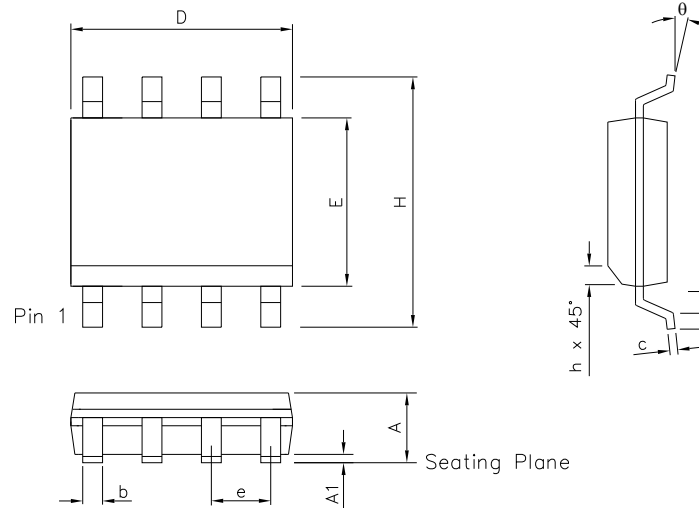


Switching time waveforms



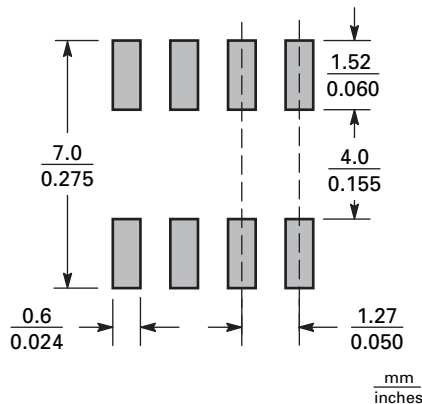
Switching time test circuit

Package Outline Dimensions



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.053	0.069	1.35	1.75	e	0.050 BSC		1.27 BSC	
A1	0.004	0.010	0.10	0.25	b	0.013	0.020	0.33	0.51
D	0.189	0.197	4.80	5.00	c	0.008	0.010	0.19	0.25
H	0.228	0.244	5.80	6.20	theta	0°	8°	0°	8°
E	0.150	0.157	3.80	4.00	h	0.010	0.020	0.25	0.50
L	0.016	0.050	0.40	1.27	-	-	-	-	-

Suggested Pad Layout



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